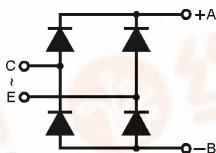


Single Phase Rectifier Bridge

I_{dAV} = 65 A
V_{RRM} = 800-1600 V

Preliminary data

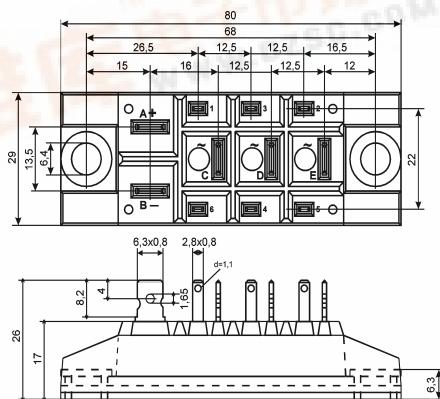
V _{RSM}	V _{RRM}	Types
V	V	
900	800	VBO 65-08N07
1300	1200	VBO 65-12N07
1500	1400	VBO 65-14N07
1700	1600	VBO 65-16N07
1900	1800	VBO 65-18N07



Symbol	Test Conditions	Maximum Ratings		
I _{dAV} *	T _C = 100°C, module	65	A	
I _{FSM}	T _{VJ} = 45°C; V _R = 0	1000	A	
	t = 10 ms (50 Hz), sine	1100	A	
	t = 8.3 ms (60 Hz), sine	700	A	
	T _{VJ} = T _{VJM} ; V _R = 0	750	A	
I ² t	T _{VJ} = 45°C; V _R = 0	5000	A ² s	
	t = 10 ms (50 Hz), sine	5000	A ² s	
	t = 8.3 ms (60 Hz), sine	2450	A ² s	
	T _{VJ} = T _{VJM} ; V _R = 0	2330	A ² s	
T _{VJ}		-40...+150	°C	
T _{VJM}		150	°C	
T _{stg}		-40...+125	°C	
V _{ISOL}	50/60 Hz, RMS I _{ISOL} ≤ 1 mA	2500	V~	
	t = 1 min t = 1 s	3000	V~	
M _d	Mounting torque (M5) (10-32 UNF)	5 ± 15 % 44 ± 15 %	Nm lb.in.	
Weight	typ.	110	g	

Symbol	Test Conditions	Characteristic Values		
I _R	V _R = V _{RRM} ; T _{VJ} = 25°C V _R = V _{RRM} ; T _{VJ} = T _{VJM}	≤ 0.5 ≤ 10	mA	
V _F	I _F = 150 A; T _{VJ} = 25°C	≤ 1.4	V	
V _{T0}	For power-loss calculations only	0.8	V	
r _T	T _{VJ} = T _{VJM}	5	mΩ	
R _{thJC}	per diode; DC current	1.12	K/W	
	per module	0.28	K/W	
R _{thJK}	per diode, DC current	1.5	K/W	
	per module	0.375	K/W	
d _s	Creeping distance on surface	16.1	mm	
d _A	Creepage distance in air	7.5	mm	
a	Max. allowable acceleration	50	m/s ²	

Dimensions in mm (1 mm = 0.0394")



Data according to IEC 60747 refer to a single diode unless otherwise stated
* For resistive load at bridge output. IXYS reserves the right to change limits, test conditions and dimensions.